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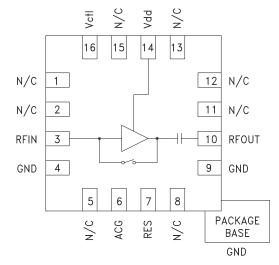
# GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 1700 - 2200 MHz

### **Typical Applications**

The HMC669LP3(E) is ideal for:

- Cellular/3G and LTE/WiMAX/4G
- BTS & Infrastructure
- Repeaters and Femtocells
- Tower Mounted Amplifiers
- Test & Measurement Equipment

#### **Functional Diagram**



#### Features

Noise Figure: 1.4 dB Output IP3: +29 dBm Gain: 17 dB Failsafe Operation: Bypass is enabled when LNA is unpowered Single Supply: +3V or +5V 16 Lead 3x3mm QFN Package: 9 mm<sup>2</sup>

### **General Description**

The HMC669LP3(E) is a versatile, high dynamic range GaAs MMIC Low Noise Amplifier that integrates a low loss LNA bypass mode on the IC. The amplifier is ideal for receivers and LNA modules operating between 1.7 and 2.2 GHz and provides 1.4 dB noise figure, 17 dB of gain and +29 dBm IP3 from a single supply of +5V @ 86mA. Input and output return losses are excellent and no external matching components are required. A single control line is used to switch between LNA mode and a low loss bypass mode. Failsafe topology also enables the LNA bidirectional bypass path when no DC power is available.

#### Electrical Specifications, $T_A = +25^{\circ}$ C, Rbias = 15 Ohm

	LNA Mode				Dunasa Mada		Failsafe Mode						
Parameter	Vdd = +3V		Vdd = +5V		Bypass Mode		Fallsale Mode		Units				
	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	
Frequency Range		1.7 - 2.2			1.7 - 2.2			1.7 - 2.2			1.7 - 2.2		GHz
Gain	12	15		14	17		-3	-2.1		-3	-2.1		dB
Gain Variation Over Temperature		0.015			0.014			0.0008			0.0008		dB/°C
Noise Figure		1.4	1.65		1.4	1.65							dB
Input Return Loss		10			11			12			12		dB
Output Return Loss		13			13			12			12		dB
Reverse Isolation		28			30			-			-		dB
Power for 1dB Compression (P1dB) <sup>[1]</sup>		11.5			12			21			24		dBm
Third Order Intercept (IP3) <sup>[2]</sup>		25			29			25			25		dBm
Supply Current (Idd)		49	59		86	105		0.04			-		mA
Switching Speed													
LNA Mode to Bypass Mode Bypass Mode to LNA Mode		100			100			80			-		ns ns

[1] P1dB for LNA Mode is referenced to RFOUT while P1dB for Bypass and Failsafe Modes are referenced to RFIN. [2] IP3 for LNA Mode is referenced to RFOUT while IP3 for Bypass and Failsafe Modes are referenced to RFIN.

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# HMC669\* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

# COMPARABLE PARTS

View a parametric search of comparable parts.

### EVALUATION KITS

- HMC669LP3 Evaluation Board
- Two Channels, 2400MHz TDD Application

### DOCUMENTATION

#### **Data Sheet**

HMC669 Data Sheet

# TOOLS AND SIMULATIONS $\square$

• HMC669 S-Parameter

### REFERENCE MATERIALS

#### **Quality Documentation**

- Package/Assembly Qualification Test Report: 16L 3x3mm QFN Package (QTR: 11003 REV: 02)
- Package/Assembly Qualification Test Report: LP2, LP2C, LP3, LP3B, LP3C, LP3D, LP3F, LP3G (QTR: 2014-0364)
- Semiconductor Qualification Test Report: PHEMT-D (QTR: 2013-00254)

# DESIGN RESOURCES

- HMC669 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

# DISCUSSIONS

View all HMC669 EngineerZone Discussions.

### SAMPLE AND BUY

Visit the product page to see pricing options.

# TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

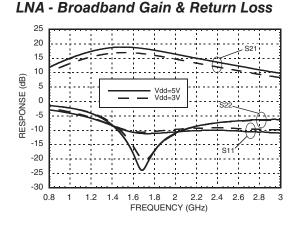
# DOCUMENT FEEDBACK

Submit feedback for this data sheet.



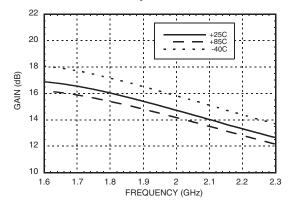


GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 1700 - 2200 MHz

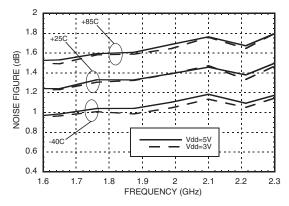


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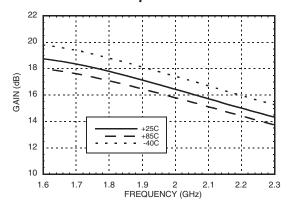
LNA - Gain vs. Temperature [2]

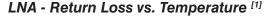


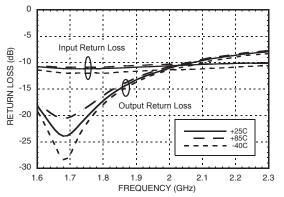
LNA - Noise Figure vs. Temperature [3]

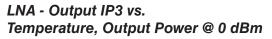


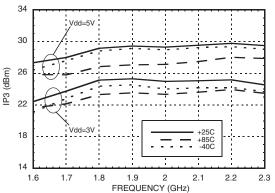
LNA - Gain vs. Temperature [1]











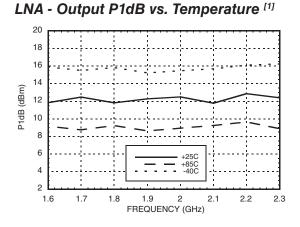
[1] Vdd = 5V [2] Vdd = 3V [3] Measurement reference plane shown on evaluation PCB drawing.

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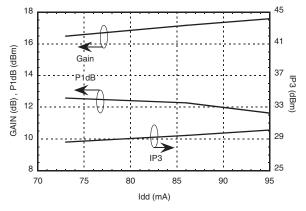


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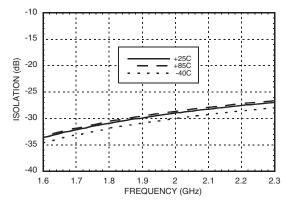


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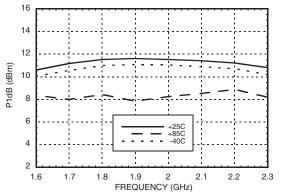
LNA - Gain, P1dB, Output IP3 vs. Current <sup>[1]</sup> @ 1900 MHz



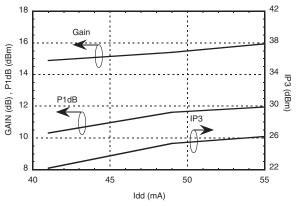
LNA - Reverse Isolation vs. Temperature [1]

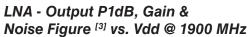


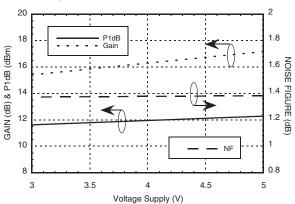
LNA - Output P1dB vs. Temperature [2]



LNA - Gain, P1dB, Output IP3 vs. Current <sup>[2]</sup> @ 1900 MHz







[1] Vdd = 5V [2] Vdd = 3V [3] Measurement reference plane shown on evaluation PCB drawing.

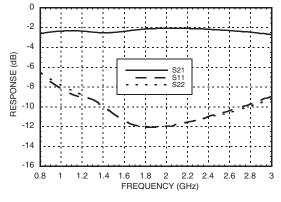
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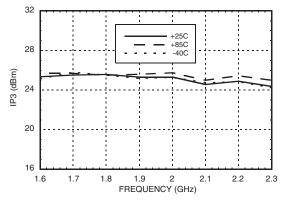
GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 1700 - 2200 MHz

Bypass Mode -Broadband Gain & Return Loss

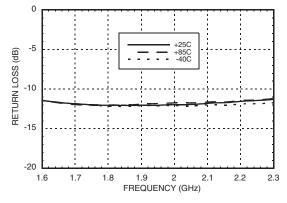


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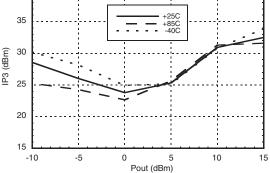
Bypass Mode - Input IP3 vs. Temperature, Output Power @ 5 dBm



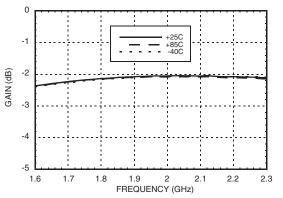
Bypass Mode -Input Return Loss vs. Temperature

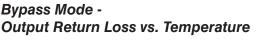


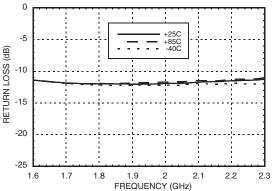
Bypass Mode -Input IP3 vs. Output Power @ 1900 MHz



Bypass Mode -Insertion Loss vs. Temperature







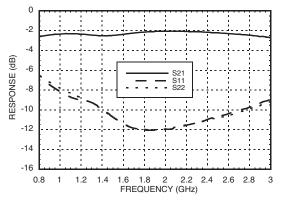
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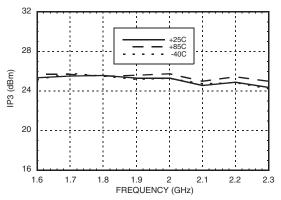
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Failsafe Mode -Broadband Gain & Return Loss

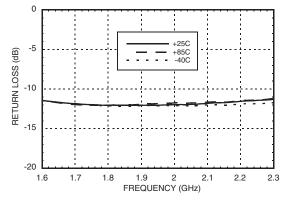


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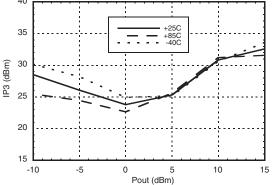
Failsafe Mode - Input IP3 vs. Temperature, Output Power @ 5 dBm



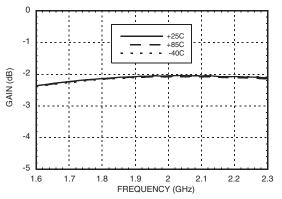
Failsafe Mode -Input Return Loss vs. Temperature



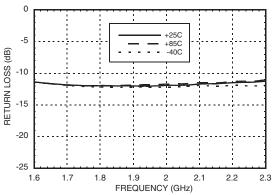
Failsafe Mode -Input IP3 vs. Output Power @ 1900 MHz



Failsafe Mode -Insertion Loss vs. Temperature



Failsafe Mode -Output Return Loss vs. Temperature



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### Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+6 Vdc		
Control Voltage (Vctl)	+6 Vdc		
RF Input PowerLNA Mode(RFIN)Bypass / Fail safe Mode	+5 dBm +20 dBm		
Channel Temperature	150 °C		
Continuous Pdiss (T = 85 °C) (derate 10.71 mW/°C above 85 °C)	0.70 W		
Thermal Resistance (channel to ground paddle)	93.33 °C/W		
Storage Temperature	-65 to +150° C		
Operating Temperature	-40 to +85° C		
ESD Sensitivity (HBM)	Class 1A		

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ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

### Typical Supply Current vs. Vdd

Rbias Ω	ldd (mA)			
RDIAS 12	Vdd= 3V	Vdd= 5V		
0	55	95		
15	49	86		
47	41	73		
180 [1]	28	50		

[1] Recommended maximum Rbias

### Truth Table

LNA Mode	VctI = Vdd = 3 to 5V		
Bypass Mode	VctI= 0V, Vdd = 3 to 5V		
Failsafe Mode	VctI = Vdd = N/C		

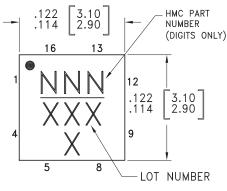
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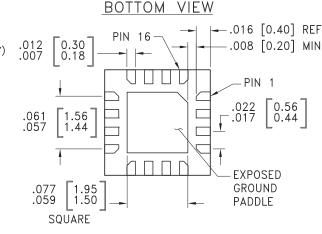


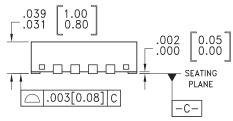


# GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 1700 - 2200 MHz

### **Outline Drawing**







#### NOTES:

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1. LEADFRAME MATERIAL: COPPER ALLOY

- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM.
- PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.

5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.

- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN.

#### Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]	
HMC669LP3	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 <sup>[1]</sup>	669 XXXX	
HMC669LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 <sup>[2]</sup>	<u>669</u> XXXX	

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 1700 - 2200 MHz

### **Pin Descriptions**

	<b>—</b>		
Pin Number	Function	Description	Interface Schematic
1, 2, 5, 8, 11, 12, 13, 15	N/C	These pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
3	RFIN	This pin is DC coupled. Off-chip DC blocking capacitor required.	RFIN O
4, 9	GND	These pins and the exposed ground paddle must be connected to RF/DC ground.	
6	ACG	AC Ground. Attach bypass capacitor per application circuit.	
7	RES	External resistor pin for current control. See table for external resistor value vs. bias current data.	ESD ACG RES
10	RFOUT	This pin is matched to 50 Ohms	
14	Vdd	Power Supply voltage pin. External bypass capacitors required.	Vdd Q
16	Vctl	Control voltage pin for LNA / Bypass Modes. Setting voltage equal to VDD enables LNA Mode. External Bypass capacitor required.	

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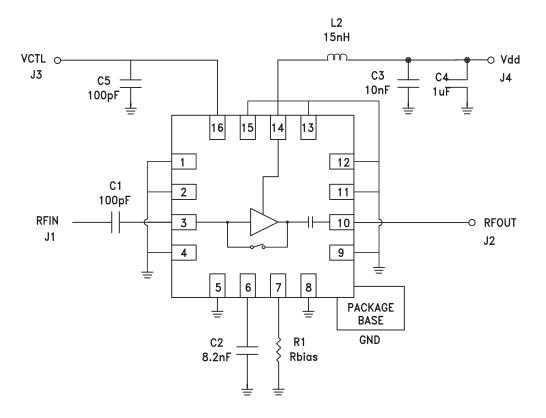


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GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 1700 - 2200 MHz

# Application Circuit



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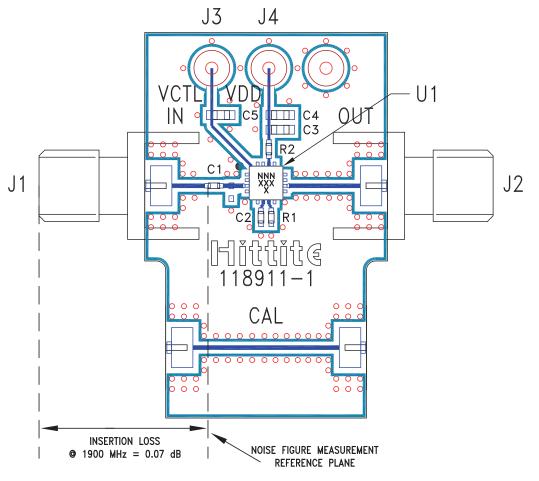


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### **Evaluation PCB**



#### List of Materials for Evaluation PCB 121923 [1]

Item	Description			
J1 - J2	PCB Mount SMA Connector			
J3 - J4	DC Pin			
C1	82 pF Capacitor, 0402 Pkg.			
C2	8200 pF Capacitor, 0402 Pkg.			
C3	10 nF Capacitor, 0603 Pkg.			
C4	1 µF Capacitor, 0603 Pkg.			
C5	100 pF Capacitor, 0603 Pkg.			
R1	15 Ohm Resistor, 0402 Pkg.			
R2	0 Ohm Resistor, 0402 Pkg.			
U1	HMC669LP3(E) Amplifier			
PCB [2]	118911 Evaluation Board			

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

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The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.